

Zhigang Jia

List of Publications by Year in descending order

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12
papers

150
citations

1306789

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h-index

1199166

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12
docs citations

12
times ranked

260
citing authors

#	ARTICLE	IF	CITATIONS
1	The formation of island-shaped morphology on the surface of InGaN/GaN QWs and the enhancement of carrier localization effect caused by high-density V-shaped pits. <i>Materials Science in Semiconductor Processing</i> , 2021, 131, 105848.	1.9	4
2	Small-size graphene oxide (GO) as a hole injection layer for high-performance green phosphorescent organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , 2021, 9, 12408-12419.	2.7	7
3	Improving the internal quantum efficiency of QD/QW hybrid structures by increasing the GaN barrier thickness. <i>RSC Advances</i> , 2020, 10, 41443-41452.	1.7	2
4	Growth and optical properties of GaN pyramids using in-situ deposited SiNx layer. <i>Materials Letters</i> , 2018, 224, 86-88.	1.3	5
5	GaN epitaxial layers grown on multilayer graphene by MOCVD. <i>AIP Advances</i> , 2018, 8, .	0.6	18
6	Enhancement of carrier localization effect and internal quantum efficiency through In-rich InGaN quantum dots. <i>Superlattices and Microstructures</i> , 2018, 113, 497-501.	1.4	19
7	Understanding the Growth Mechanism of GaN Epitaxial Layers on Mechanically Exfoliated Graphite. <i>Nanoscale Research Letters</i> , 2018, 13, 130.	3.1	21
8	Surface Morphology Evolution Mechanisms of InGaN/GaN Multiple Quantum Wells with Mixture N2/H2-Grown GaN Barrier. <i>Nanoscale Research Letters</i> , 2017, 12, 354.	3.1	13
9	Effect of hydrogen treatment temperature on the properties of InGaN/GaN multiple quantum wells. <i>Nanoscale Research Letters</i> , 2017, 12, 321.	3.1	20
10	The morphologies and optical properties of three-dimensional GaN nano-cone arrays. <i>RSC Advances</i> , 2016, 6, 43272-43277.	1.7	3
11	Effect of potential barrier height on the carrier transport in InGaAs/GaAsP multi-quantum wells and photoelectric properties of laser diode. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 6901-6912.	1.3	15
12	The evolution of a GaN/sapphire interface with different nucleation layer thickness during two-step growth and its influence on the bulk GaN crystal quality. <i>RSC Advances</i> , 2015, 5, 51201-51207.	1.7	23